

### **AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

#### **LISTING OF CLAIMS:**

1. (currently amended): A dummy wafer formed by sintering a mixture containing a silicon carbide powder and a non-metallic sintering auxiliary, wherein

a coating film layer containing silicon carbide is provided on ~~the~~a surface of the dummy wafer including at least one of either upper and lower main faces of the dummy wafer by ~~the~~a chemical vapor deposition method.

2. (currently amended): The dummy wafer according to claim 1, wherein the coating film layer containing silicon carbide is provided on ~~the~~a whole perimeter of the surface of the dummy wafer including ~~the~~a side surface of the dummy wafer.

Claim 3 (canceled).

4. (withdrawn): A method for manufacturing a dummy wafer formed by sintering a mixture containing a silicon carbide powder and a non-metallic sintering auxiliary, wherein the method for manufacturing a dummy wafer has a step of providing a coating film layer containing silicon carbide with a coating film thickness of 20  $\mu\text{m}$  or more and 70  $\mu\text{m}$  or less on the surface of the dummy wafer including at least one of either upper and lower main faces of the dummy wafer by the chemical vapor deposition method.

5. (withdrawn): The method for manufacturing a dummy wafer according to claim 4, wherein the coating film thickness of the coating film layer is 20  $\mu\text{m}$  or more and 40  $\mu\text{m}$  or less.

6. (withdrawn): The method for manufacturing a dummy wafer according to claim 4 or 5, further having a step of polishing the surface of the coating film layer.

7. (withdrawn): The method for manufacturing a dummy wafer according to claim 6, wherein the coating film layer after polishing the surface has a thickness of 20  $\mu\text{m}$  or more and 70  $\mu\text{m}$  or less, and a surface roughness (Ra) of 10 nm or less.

Claim 8 (canceled).